

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI ASAT25 is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|-------------------------|-------------------------------|
| I_C | 2.6 A |
| V_{CB0} | 45 V |
| V_{CEO} | 12 V |
| V_{EBO} | 3.0 V |
| P_{DISS} | 50 W @ T _C = 25 °C |
| T_J | -65 °C to +200 °C |
| T_{STG} | -65 °C to +150 °C |
| θ_{JC} | 3.5 °C/W |

PACKAGE STYLE .250 2L FLG(A)

| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .055 / 1.40 | .065 / 1.65 |
| B | .124 / 3.15 | |
| C | .243 / 6.17 | .253 / 6.43 |
| D | .635 / 16.13 | .665 / 16.89 |
| E | .555 / 14.10 | .565 / 14.35 |
| F | .739 / 18.77 | .749 / 19.02 |
| G | .315 / 8.00 | .325 / 8.26 |
| H | .002 / 0.05 | .006 / 0.15 |
| I | .065 / 1.40 | .065 / 1.65 |
| J | .075 / 1.91 | .095 / 2.41 |
| K | | .190 / 4.83 |
| L | .245 / 6.22 | .255 / 6.48 |
| M | .092 / 2.34 | |

ORDER CODE: ASI10520

CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | | | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------------|-------------------------|-------------------------|----------|---------|---------|---------|------------|
| BV_{CB0} | I _C = 6 mA | | | 45 | | | V |
| BV_{CEO} | I _C = 6 mA | | | 12 | | | V |
| BV_{EBO} | I _E = 6 mA | | | 3.0 | | | V |
| h_{FE} | V _{CE} = 5.0 V | I _C = 1.2 A | | 15 | | 150 | --- |
| P_G | V _{CC} = 28 V | P _{OUT} = 25 W | f = 1.65 | 9.0 | | | dB |
| η_c | GHz | | | 50 | | | % |